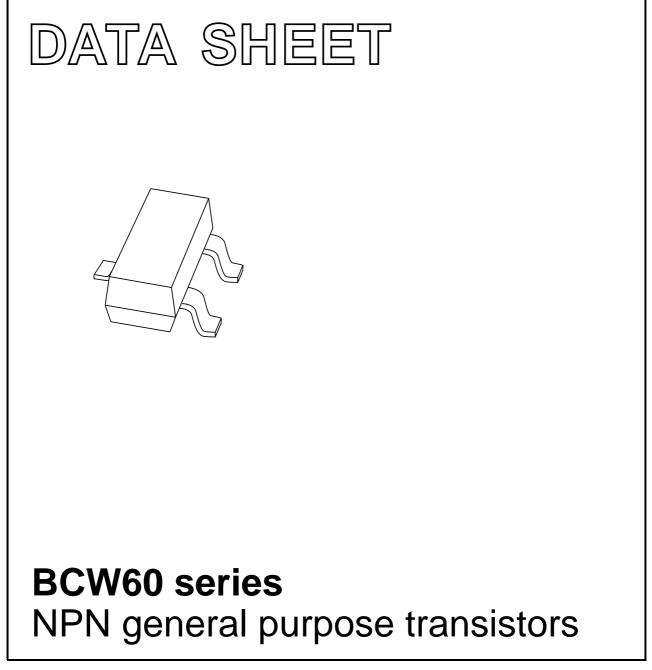
DISCRETE SEMICONDUCTORS



Product data sheet Supersedes data of 1997 Mar 10 1999 Apr 22



FEATURES

- Low current (max. 100 mA)
- Low voltage (max. 32 V).

APPLICATIONS

• General purpose switching and amplification.

DESCRIPTION

NPN transistor in a SOT23 plastic package. PNP complements: BCW61 series.

MARKING

TYPE NUMBER	MARKING CODE ⁽¹⁾
BCW60B	AB*
BCW60C	AC*
BCW60D	AD*

Note

1. * = p : Made in Hong Kong.

* = t : Made in Malaysia.

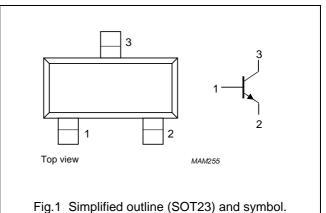
LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter	-	32	V
V _{CEO}	collector-emitter voltage	open base	-	32	V
V _{EBO}	emitter-base voltage	open collector	-	5	V
I _C	collector current (DC)		-	100	mA
I _{CM}	peak collector current		-	200	mA
I _{BM}	peak base current		-	200	mA
P _{tot}	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$	-	250	mW
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		-	150	°C
T _{amb}	operating ambient temperature		-65	+150	°C

PINNING

PIN	DESCRIPTION	
1	base	
2	emitter	
3	collector	



BCW60 series

BCW60 series

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT	
R _{th j-a}	thermal resistance from junction to ambient	note 1	500	K/W	

Note

1. Transistor mounted on an FR4 printed-circuit board.

CHARACTERISTICS

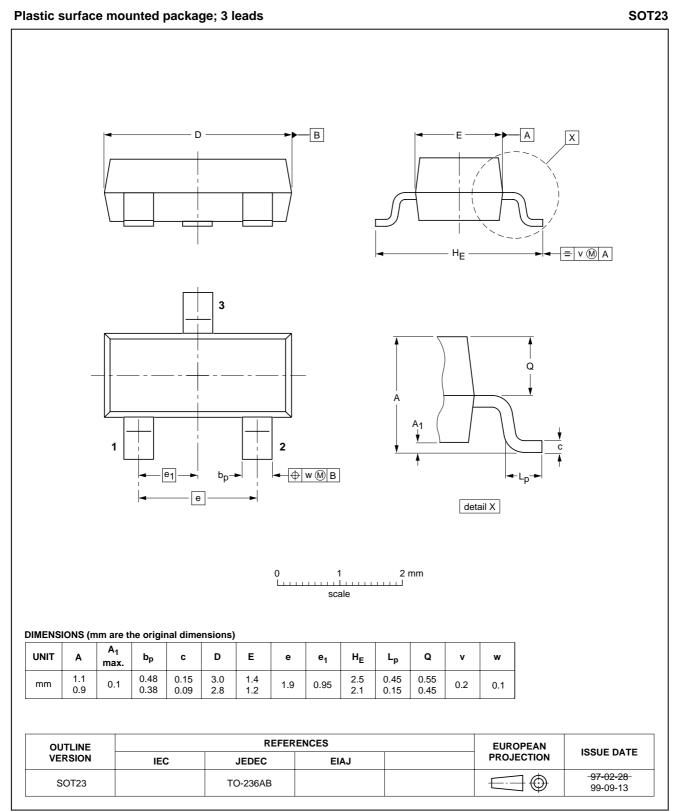
 T_{amb} = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I _{CBO}	collector cut-off current	I _E = 0; V _{CB} = 32 V	-	_	20	nA
		$I_E = 0; V_{CB} = 32 V; T_{amb} = 150 °C$	-	-	20	μA
I _{EBO}	emitter cut-off current	$I_{C} = 0; V_{EB} = 4 V$	_	_	20	nA
h _{FE}	DC current gain	$I_{C} = 10 \ \mu A; \ V_{CE} = 5 \ V$				
	BCW60B		20	-	-	
	BCW60C		40	_	_	
	BCW60D		100	_	_	
	DC current gain	I _C = 2 mA; V _{CE} = 5 V				
	BCW60B		180	_	310	
	BCW60C		250	_	460	
	BCW60D		380	_	630	
	DC current gain	I _C = 50 mA; V _{CE} = 1 V				
	BCW60B		70	_	_	
	BCW60C		90	_	_	
	BCW60D		100	_	_	
V _{CEsat}	collector-emitter saturation	I _C = 10 mA; I _B = 0.25 mA	50	_	350	mV
	voltage	I _C = 50 mA; I _B = 1.25 mA	100	_	550	mV
V _{BEsat}	base-emitter saturation voltage	I _C = 10 mA; I _B = 0.25 mA	600	_	850	mV
		I _C = 50 mA; I _B = 1.25 mA	0.7	_	1.05	V
V _{BE}	base-emitter voltage	$I_{C} = 10 \ \mu A; V_{CE} = 5 \ V$	-	520	_	mV
		I _C = 2 mA; V _{CE} = 5 V	550	650	750	mV
		I _C = 50 mA; V _{CE} = 1 V	_	780	_	mV
C _c	collector capacitance	I _E = i _e = 0; V _{CB} = 10 V; f = 1 MHz	-	1.7	_	pF
Ce	emitter capacitance	$I_{C} = i_{c} = 0; V_{EB} = 0.5 V; f = 1 MHz$	_	11	_	pF
f _T	transition frequency	I _C = 10 mA; V _{CE} = 5 V; f = 100 MHz; note 1	100	250	-	MHz
F	noise figure	I_{C} = 200 μA; V _{CE} = 5 V; R _S = 2 kΩ; f = 1 kHz; B = 200 Hz	_	2	6	dB

Note

1. Pulse test: $t_p \leq 300~\mu s;~\delta \leq 0.02.$

PACKAGE OUTLINE



BCW60 series

BCW60 series

DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

Notes

- 1. Please consult the most recently issued document before initiating or completing a design.
- The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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Customer notification

This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content, except for package outline drawings which were updated to the latest version.

Contact information

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